Pb Free Product

NCE N-Channel Super Trench Power MOSFET

Description

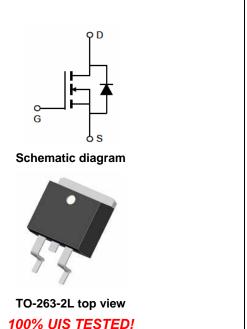
The NCEP85T14D uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

- V_{DS} =85V, I_{D} =140A $R_{DS(ON)}$ <4.0mΩ @ V_{GS} =10V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification



100% ΔVds TESTED!

Package Marking and Ordering Information

D	evice Marking	Device	Device Package	Reel Size	Tape width	Quantity
ı	NCEP85T14D	NCEP85T14D	TO-263-2L	-	-	-

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	85	V
Gate-Source Voltage	V _G S	±20	V
Drain Current-Continuous	I _D	140	Α
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	99	Α
Pulsed Drain Current	I _{DM}	420	А
Maximum Power Dissipation	P _D	200	W
Derating factor		1.3	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	1000	mJ
Operating Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 To 175	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	R _{θJC}	0.75	°C/W	Ī
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NCEP85T14D

Electrical Characteristics (T_C=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	85		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =85V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2.0	3.1	4.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =70A	-	3.3	4.0	mΩ
Forward Transconductance	g FS	V _{DS} =10V,I _D =70A	50	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	14 401/11 01/	-	5600	-	PF
Output Capacitance	Coss	V_{DS} =40V, V_{GS} =0V, F=1.0MHz	-	850	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.UIVIHZ	-	60	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	20	-	nS
Turn-on Rise Time	t _r	V_{DD} =40 V , I_D =70 A	-	10	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =4.7 Ω	-	30	-	nS
Turn-Off Fall Time	t _f		-	35	-	nS
Total Gate Charge	Qg	\/ 40\/ L 70A	-	84		nC
Gate-Source Charge	Q _{gs}	$V_{DS}=40V, I_{D}=70A,$	-	30.6		nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	18.5		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =140A	-		1.2	V
Diode Forward Current (Note 2)	I _S		-	-	140	Α
Reverse Recovery Time	t _{rr}	$T_J = 25^{\circ}C$, $I_F = I_S$	-	83		nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	194		nC

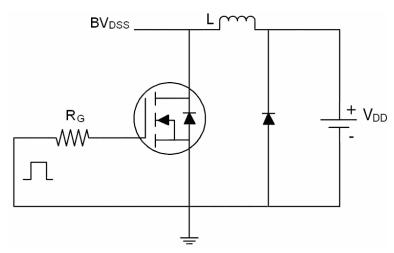
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, $t \le 10$ sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^{\circ}\text{C}$,VDD=42.5V,VG=10V,L=0.5mH,Rg=25 Ω

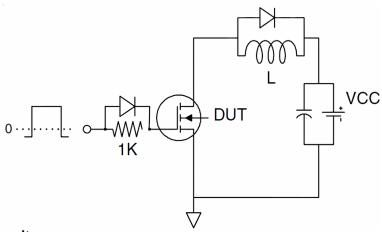


Test Circuit

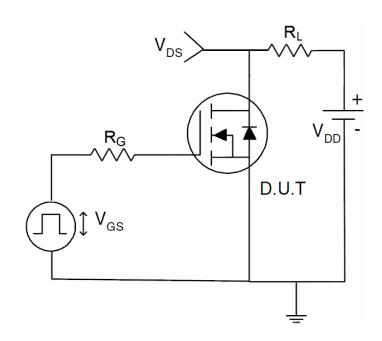
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics

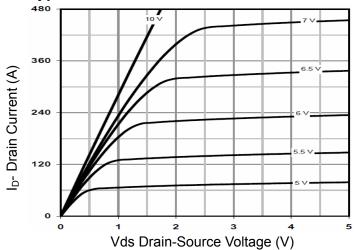


Figure 1 Output Characteristics

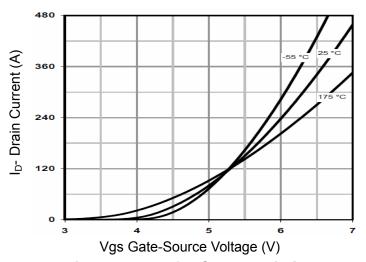


Figure 2 Transfer Characteristics

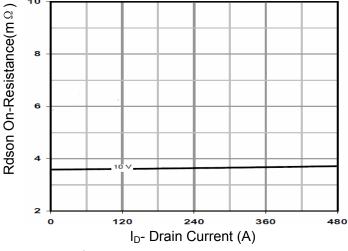


Figure 3 Rdson- Drain Current

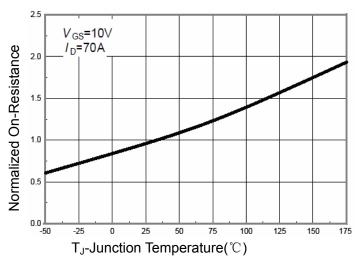


Figure 4 Rdson-JunctionTemperature

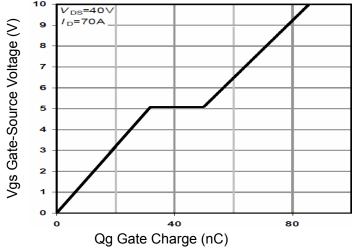


Figure 5 Gate Charge

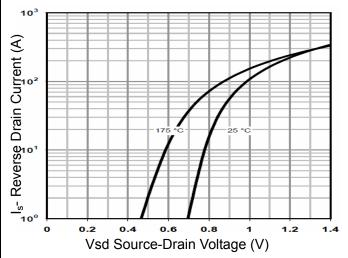
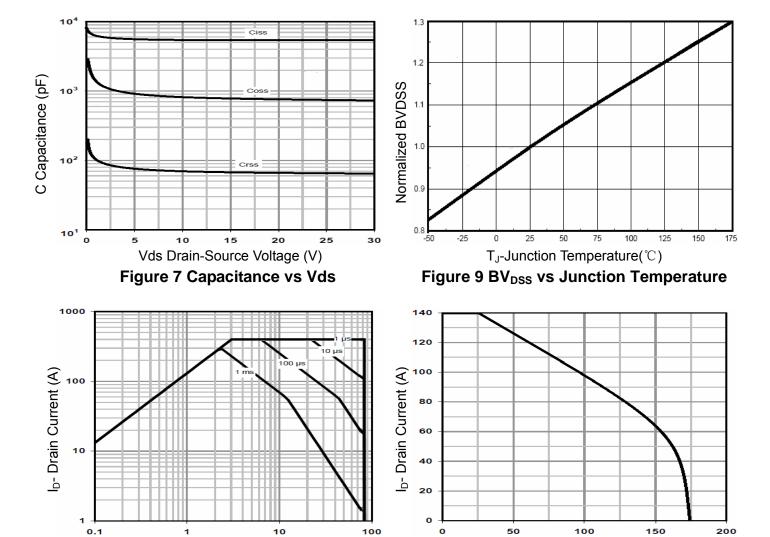


Figure 6 Source- Drain Diode Forward







T_J-Junction Temperature(°C)

Figure 10 Current De-rating

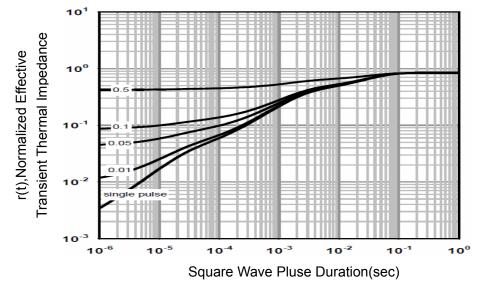


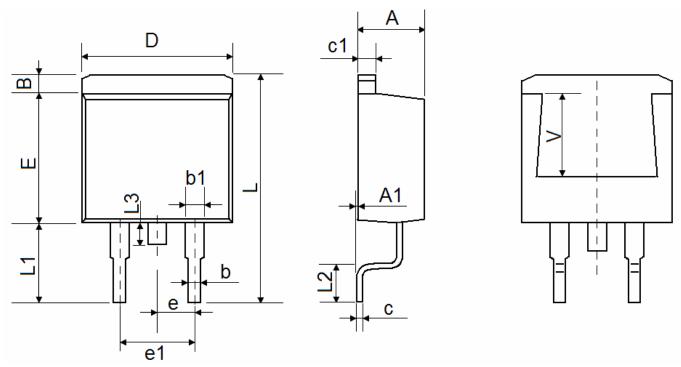
Figure 11 Normalized Maximum Transient Thermal Impedance

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NCEP85T14D

TO-263-2L Package Information



Cumbal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.470	4.670	0.176	0.184	
A1	0.000	0.150	0.000	0.006	
В	1.170	1.370	0.046	0.054	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.310	0.530	0.012	0.021	
c1	1.170	1.370	0.046	0.054	
D	10.010	10.310	0.394	0.406	
E	8.500	8.900	0.335	0.350	
е	2.540	TYP.	0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
L	15.050	15.450	0.593	0.608	
L1	5.080	5.480	0.200	0.216	
L2	2.340	2.740	0.092	0.108	
L3	1.300	1.700	0.051	0.067	
V	5.60	0 REF	0.220 REF		



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NCEP85T14D

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DMN2080UCB4-7 DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 DMP22D4UFO-7B DMN1006UCA6-7 DMN16M9UCA6-7
STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 DMN2990UFB-7B
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